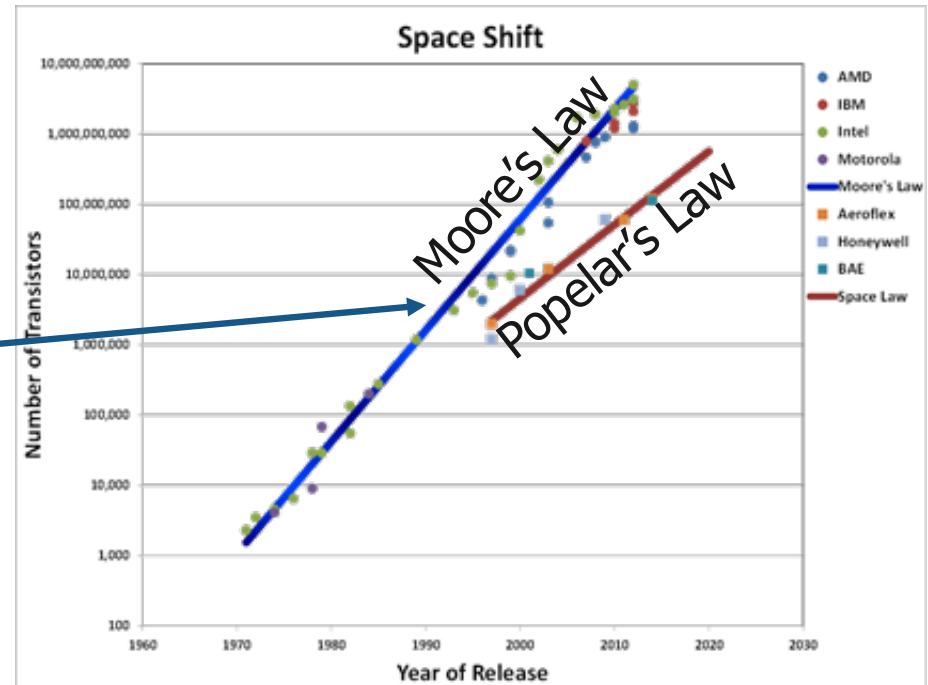




## 2017 NEPP Electronics Technology Workshop

- Cobham-NEPP collaboration projects
  - *Aeroflex Technology as Class-Y Demonstrator*
    - Completed October 2014
  - *Flip Chip on Organic Feasibility Study*
    - Completed March 2017
  - *Fine Pitch Flip Chip on Organic Development*
    - Commenced March 2017
- Acknowledgements
  - *Jong-ook Suh, Ph.D., JPL Materials Scientist and Engineer*
    - Provided invaluable guidance in scoping and executing these studies
  - *Rich Measmer, Cobham Package and Process Development Engineer*
    - Critical test vehicle procurement and assembly process development
  - *Funding provided by NASA NEPP program*
    - NEPP funding is gratefully acknowledged, without which these studies would not have been possible

- Moore's Law: The number of transistors will double every two years
- Popelar's Law: The number of transistors will quadruple every six years
- *Popelar lags Moore, and the gap is only growing*



Cobham plc

- MIL-PRF-38535 Revision K – released on December 2013
  - *Defines for the first time Class Y requirements for ceramic non-hermetic packages for space applications*
    - *Implies flip chip on ceramic assembly technology*
    - Accommodates de-coupling capacitor attach and heat sink attach
  - First DLA Class Y flip chip audit completed at Cobham Semiconductor Solutions COS facility in August 2014
    - *First DLA Class Y certification awarded to the Cobham COS facility in December 2014*
  - Stipulates that a Package Integrity Demonstration Test Plan (PIDTP) be performed for all new package technologies
    - Flip chip assembly, Chip cap attach, Heat sink attach all require PIDTP reliability assessments
    - *PIDTP reliability assessments completed by Cobham in December 2015 in support of its UT1752FC Class Y package qualification effort*

# Cobham Class Y Flip Chip Technology

## Class Y Technology as a 90nm Enabler

- *UT1752FC Class Y Non-hermetic Package Technology for Space*
  - Flip chip on ceramic, with decoupling capacitors and heat sink attach
  - 1752 pin ceramic LGA/CGA on a 1.00mm pitch; optional solder column attach
- *90nm ASIC Class Y Assembly*
  - 90nm SerDes technology, enabled by Class Y package technology
  - Product qualification scheduled to complete in 2017

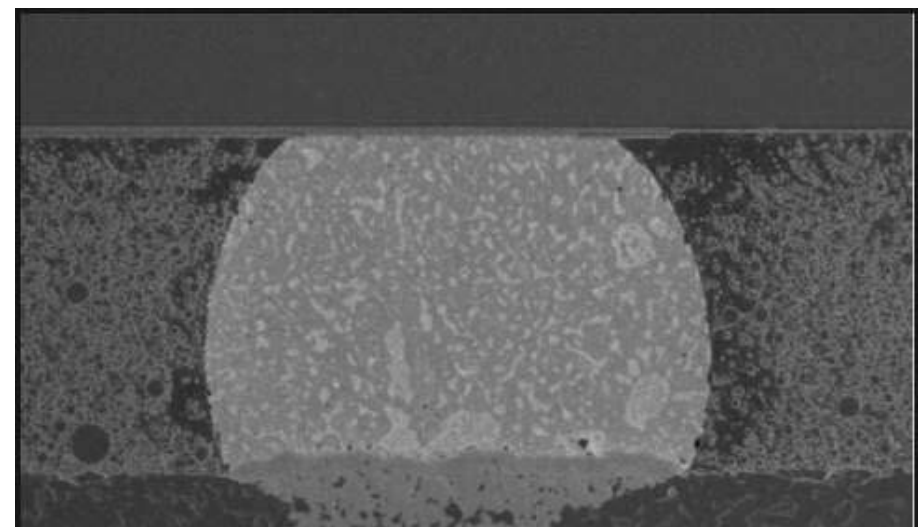
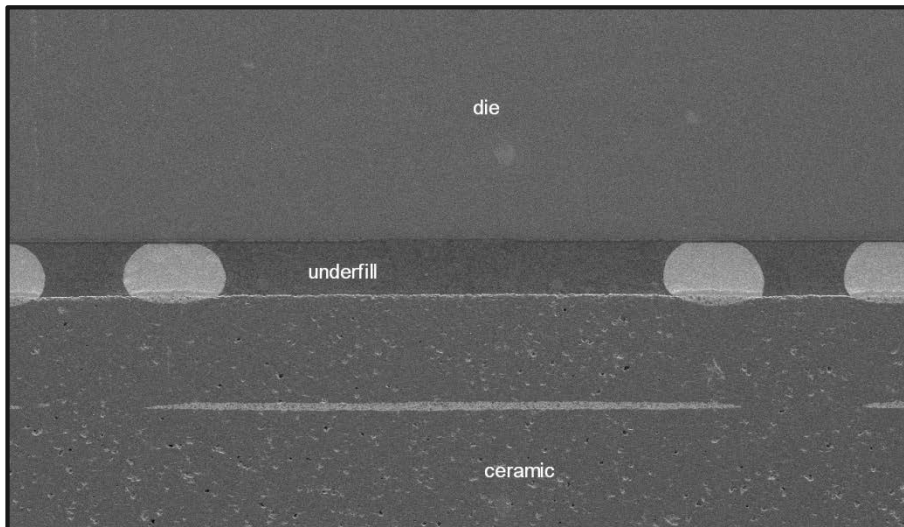
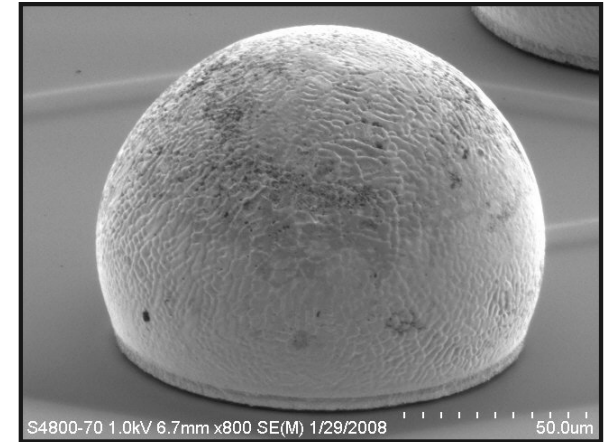
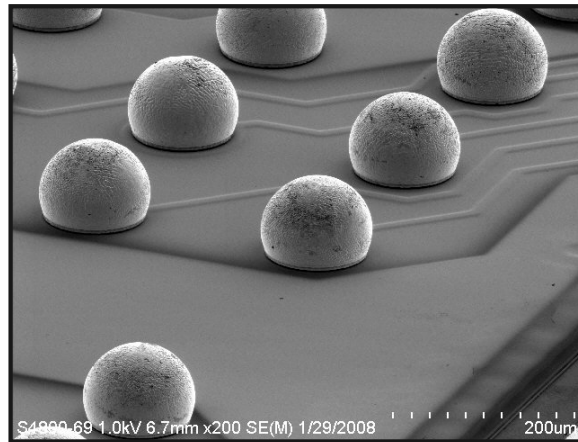
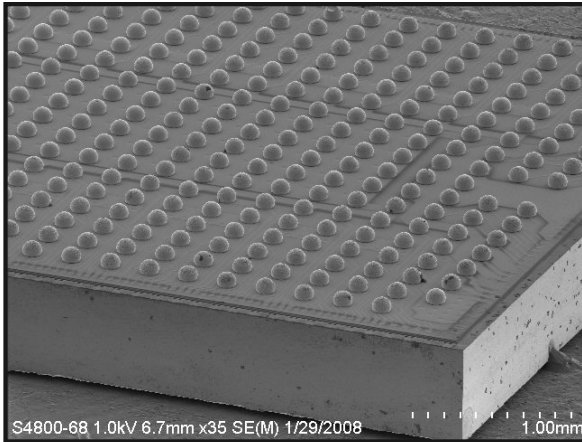




# Cobham Class Y Flip Chip Technology

## Flip Chip Assembly

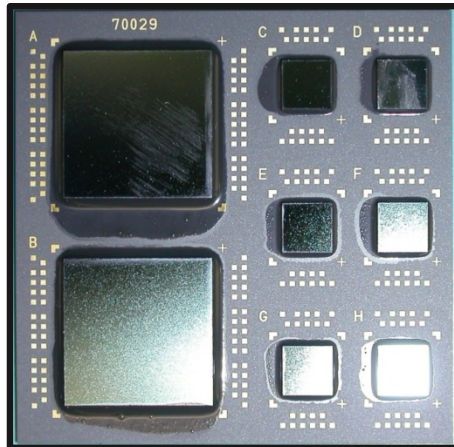
- *Solder bump flip chip interconnects – wafer bumping through assembly*



# Cobham Class Y Flip Chip Technology

## Class Y Flip Chip PIDTP

- *Flip Chip on Ceramic Daisy Chain Test Vehicles*



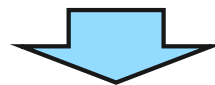
5x5mm



10x10mm



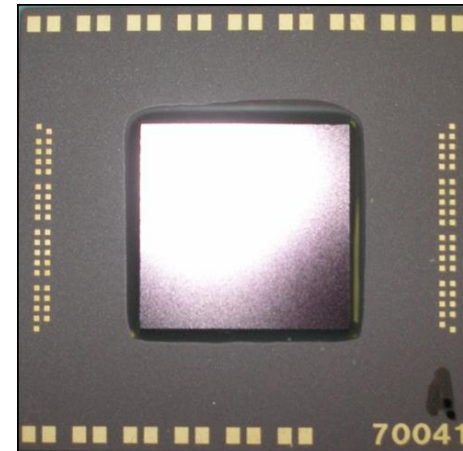
15x15mm



20x20mm



25x25mm



### • *Flip Chip PIDTP Results*

Test Type	Test Method	Criteria	Status
Wafer Level Acceptance	Bump Yield <ul style="list-style-type: none"><li>Automated optical inspection</li></ul>	Bump defect rate < 200 ppm	Pass
Wafer Level Acceptance	Bump Height <ul style="list-style-type: none"><li>Automated optical inspection</li></ul>	Nominal +/- 15 $\mu\text{m}$	Pass
Wafer Level Acceptance	Bump Shear <ul style="list-style-type: none"><li>JESD22-B117A</li></ul>	Minimum load of 3 mg/ $\mu\text{m}^2$	Pass
Die Shear Assembly Monitor	TM 2011, Condition F <ul style="list-style-type: none"><li>Pre underfill</li></ul>	Minimum load of 5 gr/bump	Pass
X-Ray Assembly Monitor	TM 2012 <ul style="list-style-type: none"><li>Post underfill</li></ul>	Solder joint voids < 25% of bump diameter	Pass
CSAM Assembly Monitor	TM 2030 <ul style="list-style-type: none"><li>Post underfill</li></ul>	Underfill void content < 10% of die area	Pass
Cross Section Assembly Monitor	IAW Aeroflex specification 49210 <ul style="list-style-type: none"><li>Post underfill</li></ul>	0 defects allowed related to solder joints or underfill	Pass



- *Flip Chip PIDTP Results (continued)*

Test Type	Test Method	Criteria	Status
Temperature Cycle	TM 1010, Condition B <ul style="list-style-type: none"><li>• 250 cycle endpoints, or as appropriate</li><li>• Test to failure, or 3000 cycles, whichever occurs first</li></ul>	Continuity endpoint testing; >15% increase in daisy chain resistance constitutes failure	Pass
125°C High Temperature Storage  150°C High Temperature Storage	JESD22-A103C <ul style="list-style-type: none"><li>• High temperature storage at 125°C and 150°C</li><li>• Endpoints at 0, 250, 500, 750, 1000, 1500 and 2000 hours</li></ul> TM 2011, Condition F <ul style="list-style-type: none"><li>• Die shear at each endpoint</li><li>• 6 die per endpoint; no underfill</li></ul>	Minimum load of 5 gr/bump	Pass
Multiple Reflow	JESD22-A113-B <ul style="list-style-type: none"><li>• Multiple reflows; eutectic profile</li><li>• Endpoints at 0, 1, 5, 10, 15 and 20 reflows</li></ul> TM 2011, Condition F <ul style="list-style-type: none"><li>• Die shear at each endpoint</li><li>• 6 die per endpoint; no underfill</li></ul>	Minimum load of 5 gr/bump	Pass

- *Collaborative effort between Cobham (Aeroflex) and NEPP/JPL to study the reliability of Cobham technology as a Class Y demonstrator*
  - NEPP/JPL Report: *Aeroflex Technology as Class-Y Demonstrator*
  - JPL Publication 14-16 9/14 (October 2014)
    - Authors: Jong-ook Suh, Scott Popelar
- *Electromigration of flip chip solder joint interconnect*
  - Electromigration characterization study
  - Effect of current stressing on flip chip solder interconnect strength
- *Synergistic effect of pre-conditioning on temperature cycle testing*
  - Moisture loading, Multiple reflows, Vacuum aging, Current stressing
- *Effect of ramp rate on temperature cycle testing*
  - 3.5°C/min fast ramp rate versus 0.2°C/min slow ramp rate

- Black's Equation

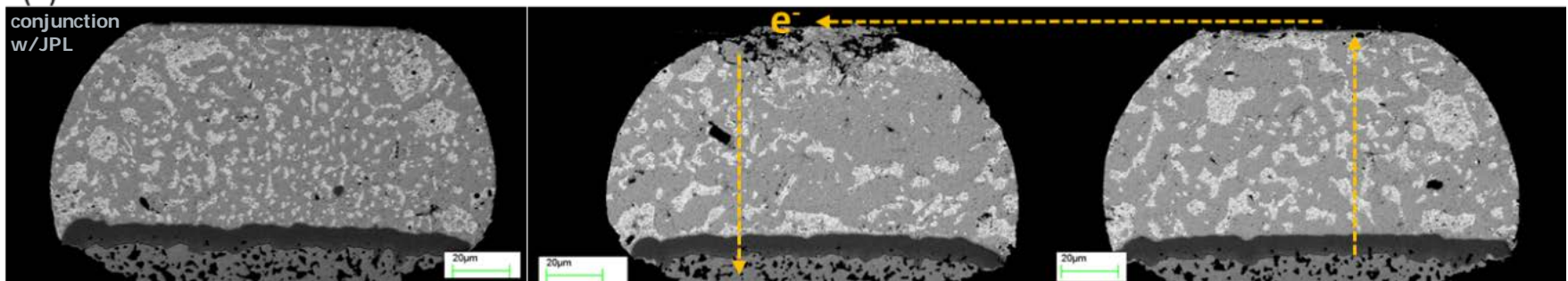
$$MTTF = Aj^{-n} \exp \frac{E_a}{kT}$$

- Accelerated current stressing conditions

- 1A passed through 639 daisy chained interconnects ( $j = 2.0 \times 10^4 \text{ A/cm}^2$ )
- Joule heating to  $115^\circ\text{C}$
- *Time to failure estimated at 5-8 days*
- *Predicted time to failure 7.5-12.4 days*

- Use conditions (example)

- 30mA current at  $80^\circ\text{C}$  junction temperature
- *Predicted time to failure 168 years*



- *TM1010 Condition B Temperature Cycle Results (-55/125°C)*
  - 15x15mm daisy chain die size
  - Comparison of fast ramp rate results below
  - *No slow ramp failures after 3000 cycles*

Precondition	Weibull Life	Weibull Slope	Weibull Fit R <sup>2</sup>
Baseline (no precondition)	3629	6.3	0.9613
Moisture Loading (27 days at 85°C/85%)	2438	7.5	0.9717
Multiple Reflow (5x eutectic reflows)	5237	6.4	0.9348
Vacuum Aging (3 months in 10 <sup>-7</sup> Torr at 135°C)	5474	8.9	0.9402
Current Stressing (96 hours at 1A and 115°C)	3978	4.9	0.8013



## Limitations of Flip Chip on Ceramic

- *Ceramic package technology limitations*

- Dielectric constant of alumina (9.8) limits performance/speeds to ~6Gbps
- Routing is limited to 50µm lines and spaces
- CTE mismatch between ceramic package (~6ppm/C) and board (~17ppm/C) becomes significant for large I/O package footprints
- Cost for ceramic packages increases exponentially with large I/O footprints

- *Solder bump flip chip pitch limitations*

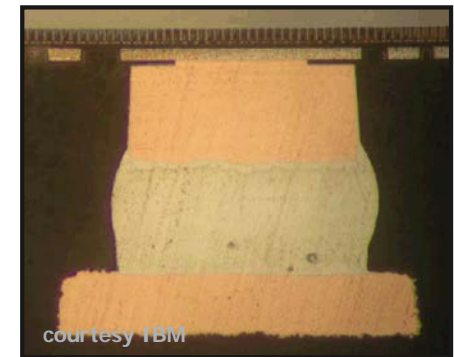
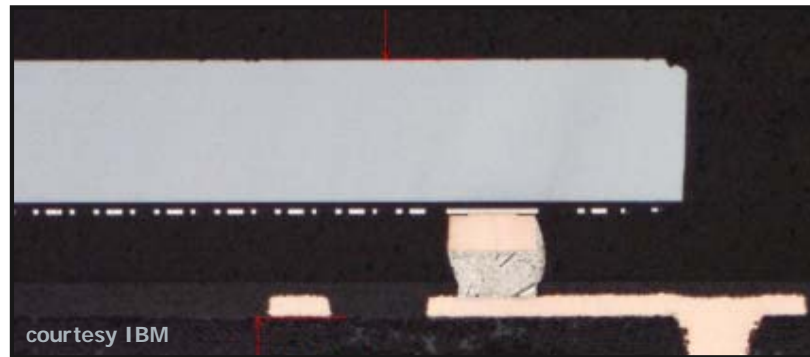
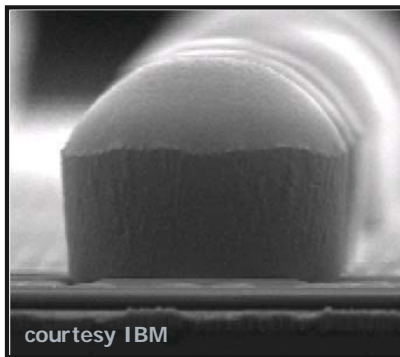
- Solder interconnects are nominally limited to pitches of 200µm if the goal is to maintain a bump height of 100µm
- Below 200µm pitches, the solder bump will have to shrink (~1/2 pitch), resulting in a corresponding decrease in reliability
- Sub-90nm technology nodes typically utilize fine pitch die I/O (150µm or less)

***Next Generation Class Y Technology required to enable sub-90nm technology***

# Next Generation Class Y Technology

Flip Chip on Organic Technology as a sub-90nm Enabler

- *Kyocera High Density Build-Up (HDBU) organic substrate technology*
  - Capable of handling speeds typical of sub-90nm technology nodes (>10Gbps)
  - Capable of routing with 12 $\mu$ m lines and spaces
  - Lower CTE mismatch between organic package (~11ppm/C) and board (~17ppm/C)
  - Lower cost solution for large I/O package footprints
- *Copper pillar flip chip interconnects*
  - Capable of handling fine pitches typical of sub-90nm technology nodes (100-150 $\mu$ m)
  - Greater electromigration resistance compared to solder bump interconnects

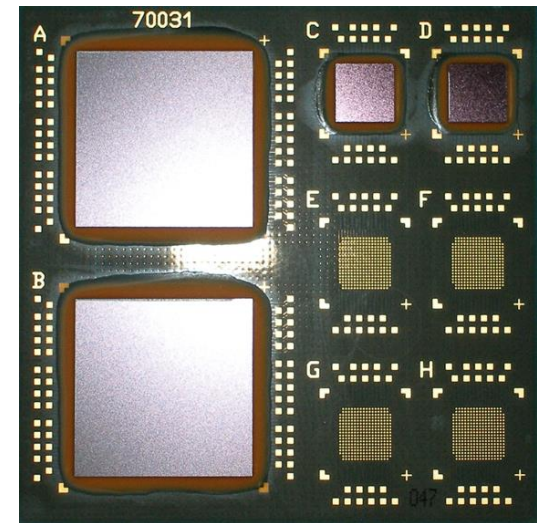
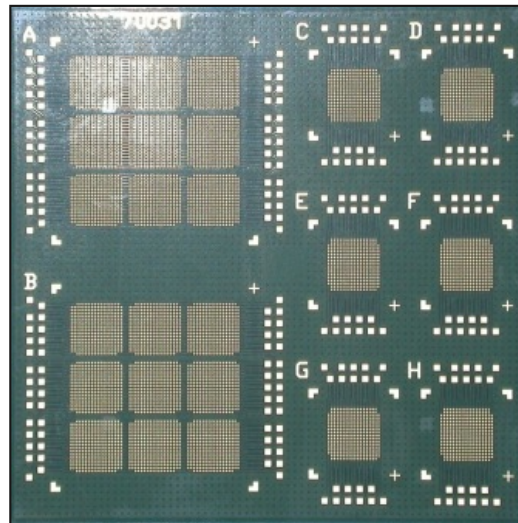
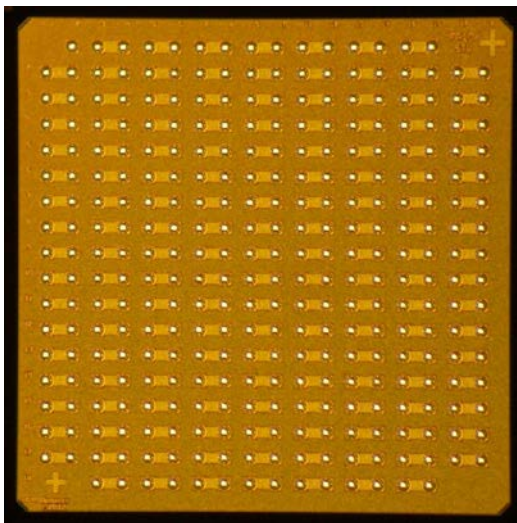


*Space Law requires qualification of Next Generation Class Y Technology*

- *Collaborative effort between Cobham and NEPP/JPL to study the feasibility of flip chip on organic technology for space applications*
  - Technical leads: Scott Popelar, Jong-ook Suh, Rich Measmer
  - Duration: December 2016 thru March 2017
  - Report: 2017 GOMACTech Conference
- *Identify and vet different underfill materials as to their compatibility and reliability with respect to flip chip on organic assembly*
  - Outgassing, Mechanical characterization
- *Establish a reliability baseline for flip chip assembly to organic substrates using existing test vehicles*
  - Stud pull and CSAM assembly monitors
  - High temperature storage, Temperature cycling, Moisture loading effect

## Test Vehicle Description

- *FA10 Flip Chip Daisy Chain Test Die*
  - 254 $\mu$ m bump pitch, 110 $\mu$ m bump height
  - Eutectic Sn/Pb solder alloy; FCI wafer bumping technology
  - 5x5mm (317 I/O) and 15x15mm (2,853 I/O) die sizes
- *Organic High Density Build-Up (HDBU) test substrate*
  - Dual-sided, 1.0mm thick
  - 127 $\mu$ m solder mask defined pads with ENIG plating

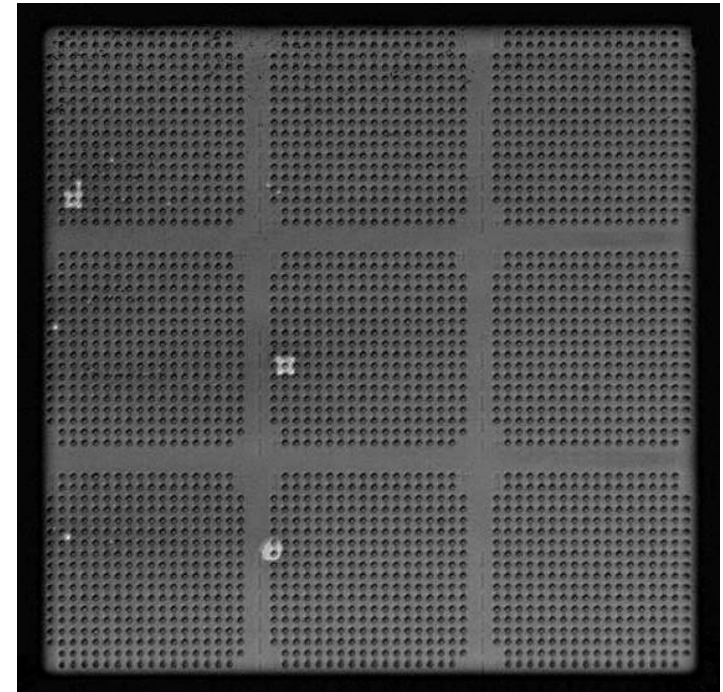
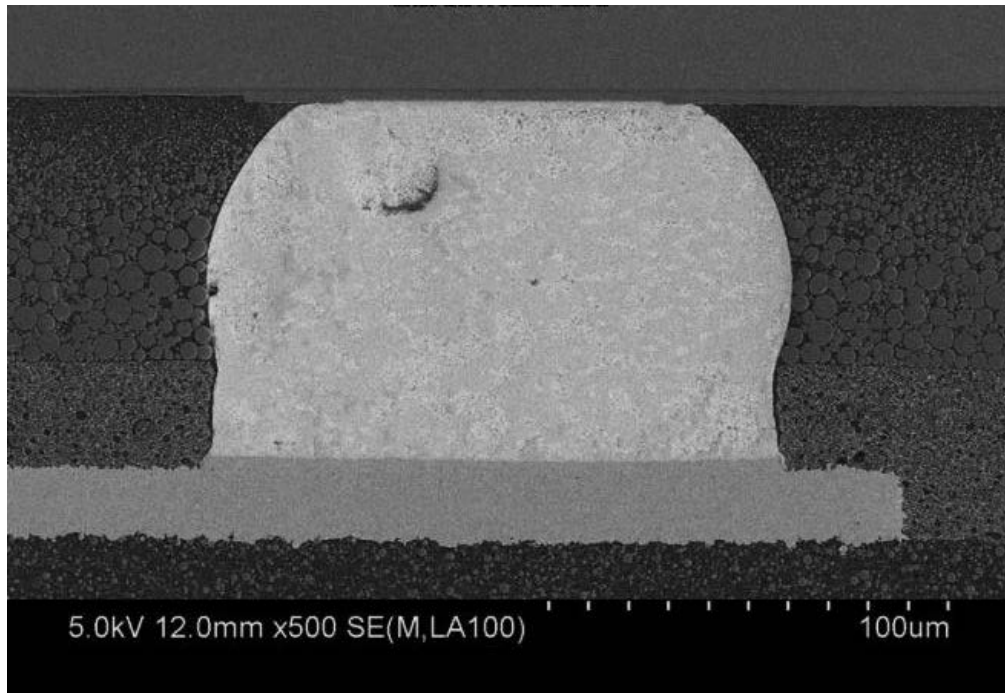




# Flip Chip on Organic Feasibility Study

## Assembly Monitors

- *Cross-section and CSAM Assembly Monitors*
  - Solder joint integrity at die and substrate interface
  - Minimal underfill void content (much less than 10% allowable)



- *Underfill Material Properties*

- “Control” qualified for Class Y applications; meets TM5011 requirements
  - $T_g = 120^{\circ}\text{C}$ ,  $\text{CTE} = 28\text{ppm/C}$
- Underfill “A” selected due to its  $T_g$  that is higher than that of the Control
  - $T_g = 135^{\circ}\text{C}$ ,  $\text{CTE} = 27\text{ppm/C}$
- Underfill “B” selected due to its CTE being lower than that of the Control
  - $T_g = 115^{\circ}\text{C}$ ,  $\text{CTE} = 22\text{ppm/C}$
- *All three underfill materials meet outgassing requirements*

Underfill	IWV per TM1018 (5000ppm limit)	TML per ASTM E-595 (1.0% limit)	CVCM per ASTM E-595 (0.1% limit)
Control	816ppm	0.24%	0.01%
A	518ppm	0.18%	0.00%
B	612ppm	0.19%	0.01%

# Flip Chip on Organic Feasibility Study

## Reliability Baseline

### • *Reliability Assessments*

Test Type	Test Method	Criteria	Status
Flip Chip Pull-Off Test Assembly Monitor	MIL-STD-883, TM 2031 <ul style="list-style-type: none"><li>• Pre underfill</li></ul>	Minimum load of 18.1kg	Pass
CSAM Assembly Monitor	MIL-STD-883, TM 2030 <ul style="list-style-type: none"><li>• Post underfill</li></ul>	Underfill void content < 10% of die area	Pass
Stud Pull Test Assembly Monitor	MIL-STD-883, TM 2027 <ul style="list-style-type: none"><li>• Post underfill</li></ul>	Minimum load of 10.7kg	Pass
Cross Section Assembly Monitor	IAW Cobham specification 49210 <ul style="list-style-type: none"><li>• Post underfill</li></ul>	0 defects allowed related to solder joints or underfill	Pass
High Temperature Storage Testing	JEDEC JESD22-A103C <ul style="list-style-type: none"><li>• High temperature storage at 125°C and 150°C</li><li>• Endpoints every 250 hours, up to 2000 hours; extended testing to 4000 hours</li></ul>	Continuity endpoint testing; >15% increase in daisy chain resistance constitutes failure	Pass 4000 hrs at 125°C

# Flip Chip on Organic Feasibility Study

## Reliability Baseline

### • *Reliability Assessments (continued)*

Test Type	Test Method	Criteria	Status
Temperature Cycle Testing Fast Ramp Rate (~3.5C/sec) Slow Ramp Rate (~0.2C/sec)	MIL-STD-883, TM 1010, Condition B (-55/125°) <ul style="list-style-type: none"><li>• 250 cycle endpoints, or as appropriate</li><li>• Test to failure, or 3000 cycles, whichever occurs first</li><li>• Failure analysis</li></ul>	Continuity endpoint testing; >15% increase in daisy chain resistance constitutes failure	Refer to following slides
Moisture Loading	JEDEC JESD22-A101 <ul style="list-style-type: none"><li>• 1000 hours at 85°C/85%RH</li><li>• Endpoint testing at 0 and 1000 hours</li><li>• Continuity testing</li><li>• Stud pull testing per TM 2027</li></ul>	Continuity endpoint testing; >15% increase in daisy chain resistance constitutes failure	Pass
Moisture Loading Temperature Cycle Testing	JEDEC JESD22-A101 <ul style="list-style-type: none"><li>• 1000 hours at 85°C/85%RH</li></ul> MIL-STD-883, TM 1010, Condition B (-55/125°C) <ul style="list-style-type: none"><li>• 250 cycle endpoints</li><li>• Test to 3000 cycles</li></ul>	Continuity endpoint testing; >15% increase in daisy chain resistance constitutes failure	Refer to following slides



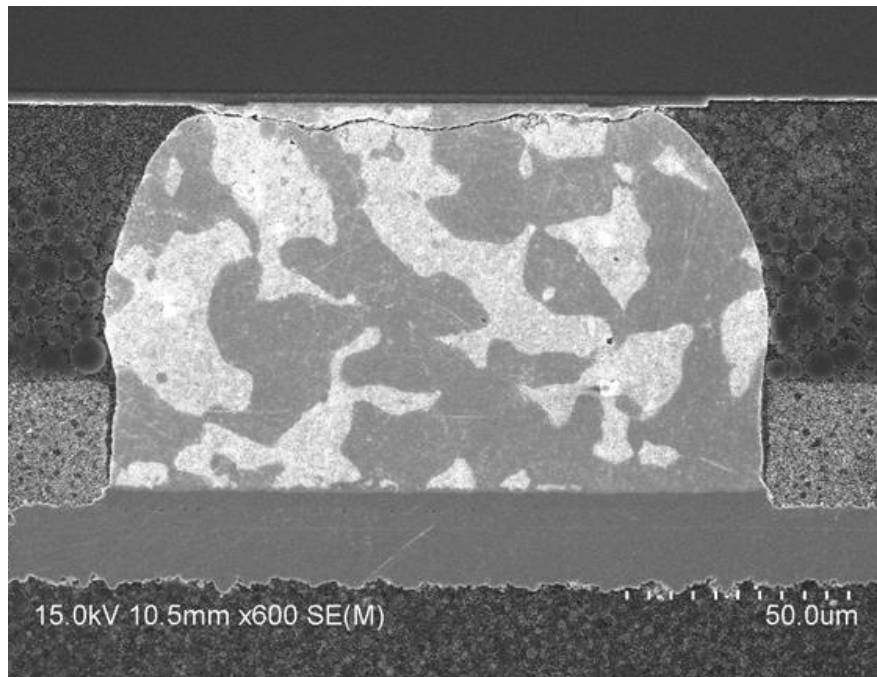
- *125°C High Temperature Storage Testing*
  - 4000 hours completed with no failures detected
- *150°C High Temperature Storage Testing*
  - First failure detected at 750 hour endpoint
  - Failures indicative of UBM consumption due to thermal migration
- *No HTS dependence on underfill material observed*
  - All three underfill materials pass 4000 hours at 125°C
  - Failures at 750 hours at 150°C with all three underfill materials
- *No HTS dependence on substrate material observed*
  - Flip chip on organic results consistent with flip chip on ceramic results
  - No failures at 125°C after 4000 hours
  - HTS at 150°C limited by UBM consumption

- *Fast Ramp Rate Condition B Temperature Cycle Testing (-55/125°C)*
  - 3000 fast ramp rate cycles completed ( $\sim 3.5^{\circ}\text{C}/\text{sec}$ )
- *Die Size Dependence Observed (5x5mm vs 15x15mm die size)*
  - No failures with 5x5mm die, across all underfill materials
- *Underfill Dependence Observed (15x15mm die size)*
  - Control: First failure at 250 cycle endpoint; 70% failure at 3000 cycles
  - A: First failure at 2000 cycle endpoint; 30% failure at 3000 cycles
  - B: First failure at 2250 cycle endpoint; 10% failure at 3000 cycles
- *Slow Ramp Rate Condition B Temperature Cycle Testing (-55/125°C)*
  - 3000 slow ramp rate cycles completed ( $\sim 0.2^{\circ}\text{C}/\text{sec}$ )
  - Similar failure rates compared to fast ramp rate temperature cycle testing

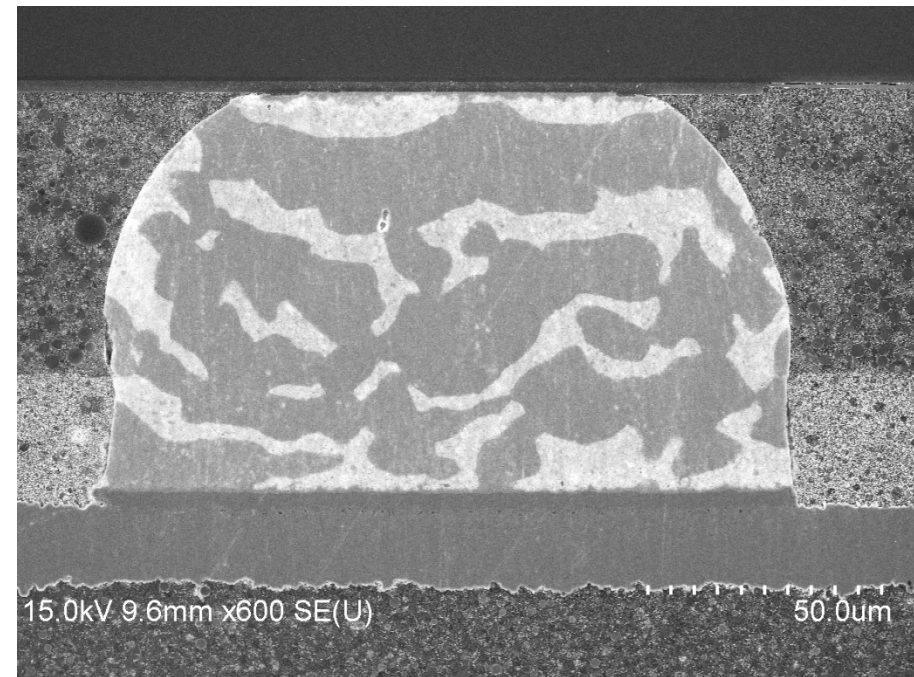
***Underfill B exhibits superior resistance to temperature cycling***

## Temperature Cycle Testing

- *Fast Ramp Rate Temperature Cycle Cross Section Failure Analysis*
  - Significant grain coarsening between lead and tin components (typical)
  - Interconnect failure due to underfill delamination (Underfill A)

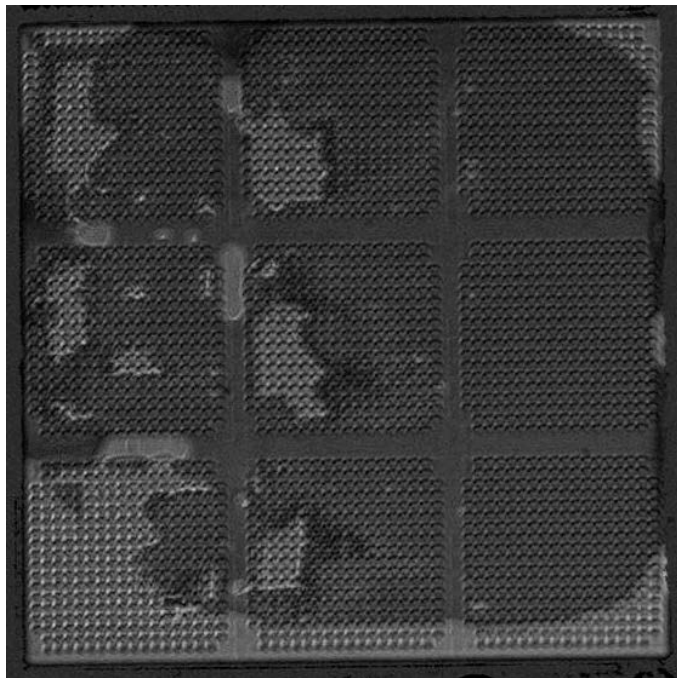


Failed solder interconnect after 3000 cycles  
(Underfill A)

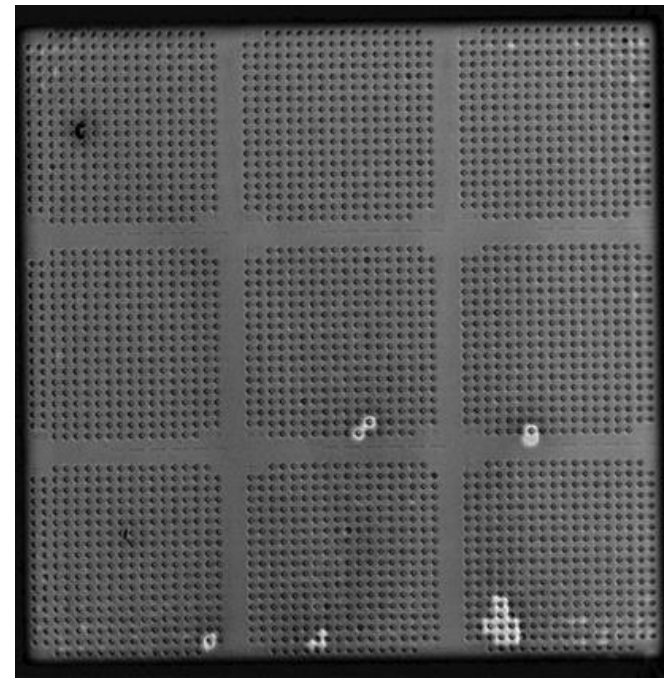


Passing solder interconnect after 3000 cycles  
(Underfill B)

- *Fast Ramp Rate Temperature Cycle CSAM Failure Analysis*
  - CSAM analysis performed after 3000 cycle endpoint
  - Evidence of delamination with Underfill A
  - No evidence of underfill delamination with Underfill B



Sample with underfill delamination



Sample without underfill delamination



- *Moisture Loading*
  - 1000 hours completed at 85°C/85%RH moisture loading
  - All parts pass continuity testing and stud pull monitor
- *Effect on Fast Ramp Rate Temperature Cycle Testing (3000 cycles)*
  - Accelerated failure rate with Control and Underfill A
  - No effect on failure rate observed with Underfill B
- *Effect on Slow Ramp Rate Temperature Cycle Testing (3000 cycles)*
  - Control underfill exhibited improvement with moisture loading
  - Accelerated failure rate with Underfill A
  - No effect on failure rate observed with Underfill B

*Underfill B exhibits superior resistance to moisture loading effects*

# Flip Chip on Organic Feasibility Study

## Class Y and Organic Flip Chip Comparison

- *Condition B Temperature Cycle Results after 3000 cycles (% failures)*

3000 Temperature Cycle Endpoint 15x15mm Daisy Chain Die Size					
Ramp Rate	Underfill	w/o Moisture Loading		w/ Moisture Loading	
		Class Y	Organic	Class Y	Organic
Fast	Control	40%	70%	100%	100% (250TC)
	A	n/a	30%	n/a	100% (500TC)
	B	n/a	10%	n/a	10%
Slow	Control	0%	100%	0%	10%
	A	n/a	80%	n/a	100% (1000TC)
	B	n/a	10%	n/a	10%

- Conclusions

- *The study demonstrates the feasibility of flip chip on organic substrate technology for use in space applications*
  - Underfill B flip chip on organic assemblies exhibit comparable reliability to Class Y flip chip on ceramic assemblies with the Control underfill
- Underfill selection with respect to temperature cycle resistance and influence of moisture loading is critical
  - Underfill B clearly outperforms Control and Underfill A materials
  - Underfill B has better compatibility with respect to adhesion and CTE mismatch

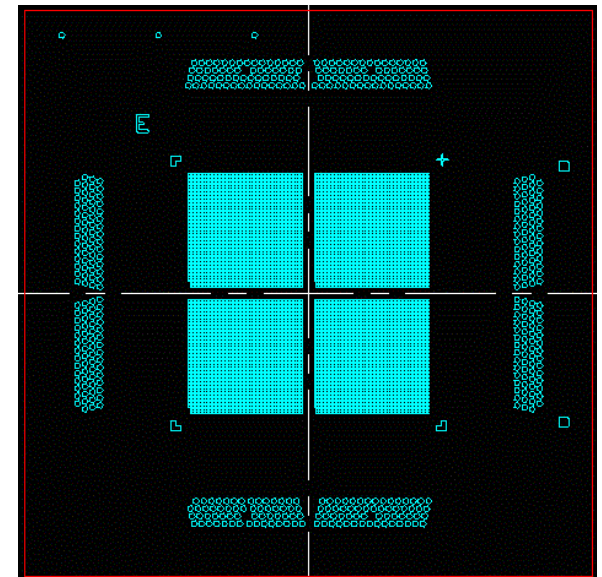
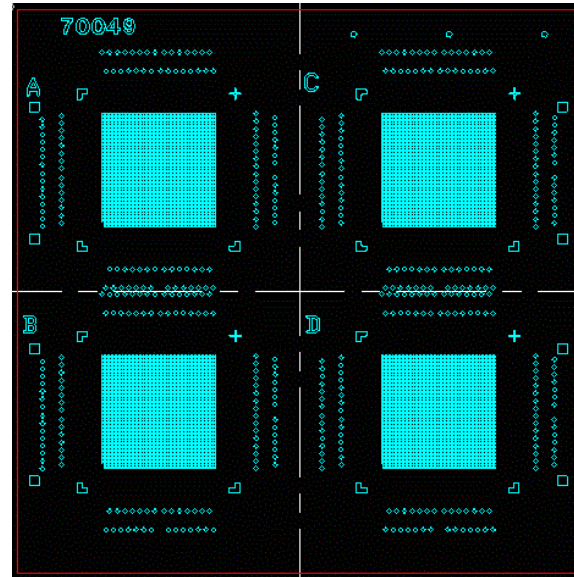
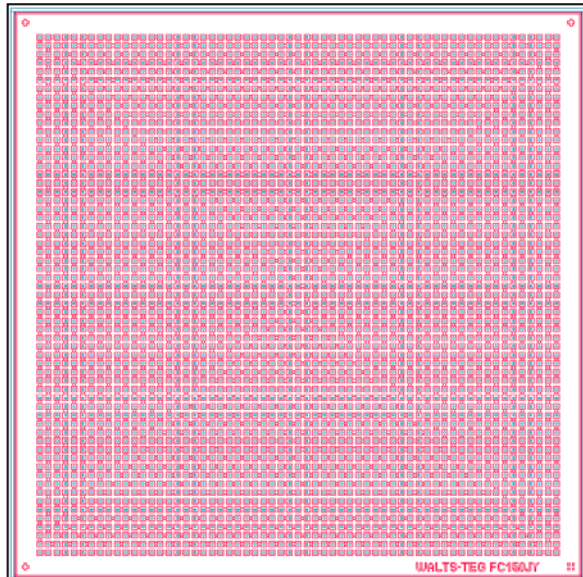
- Next Steps

- Perform reliability assessment utilizing fine pitch daisy chain test vehicle
- *Evaluate copper pillar flip chip interconnects*

*Kick off Fine Pitch Flip Chip on Organic Development project*

- *Collaboration between Cobham and NEPP/JPL to evaluate the reliability of fine pitch flip chip on organic technology for space applications*
  - Technical leads: Scott Popelar, Jong-ook Suh, Rich Measmer
  - Duration: March 2017 thru June 2018
- *Test Vehicle Design and Procurement*
  - Procure fine pitch (150µm) daisy chain test vehicle from Practical Components
  - Design and procure daisy chain HDBU organic test substrate from Kyocera
  - Evaluate supply chain for eutectic Sn/Pb copper pillar wafer bumping
- *Copper Pillar Assembly Development*
  - Vet flux and underfill material options for copper pillar assembly
  - Develop copper pillar flip chip assembly processes
  - Optimize underfill process with respect to voiding, etc.
- *Reliability Assessments*
  - Test vehicle assembly and assembly monitors
  - Assess fine pitch copper pillar flip chip on organic reliability
    - High Temp Storage, Moisture Loading, Temperature Cycle Testing

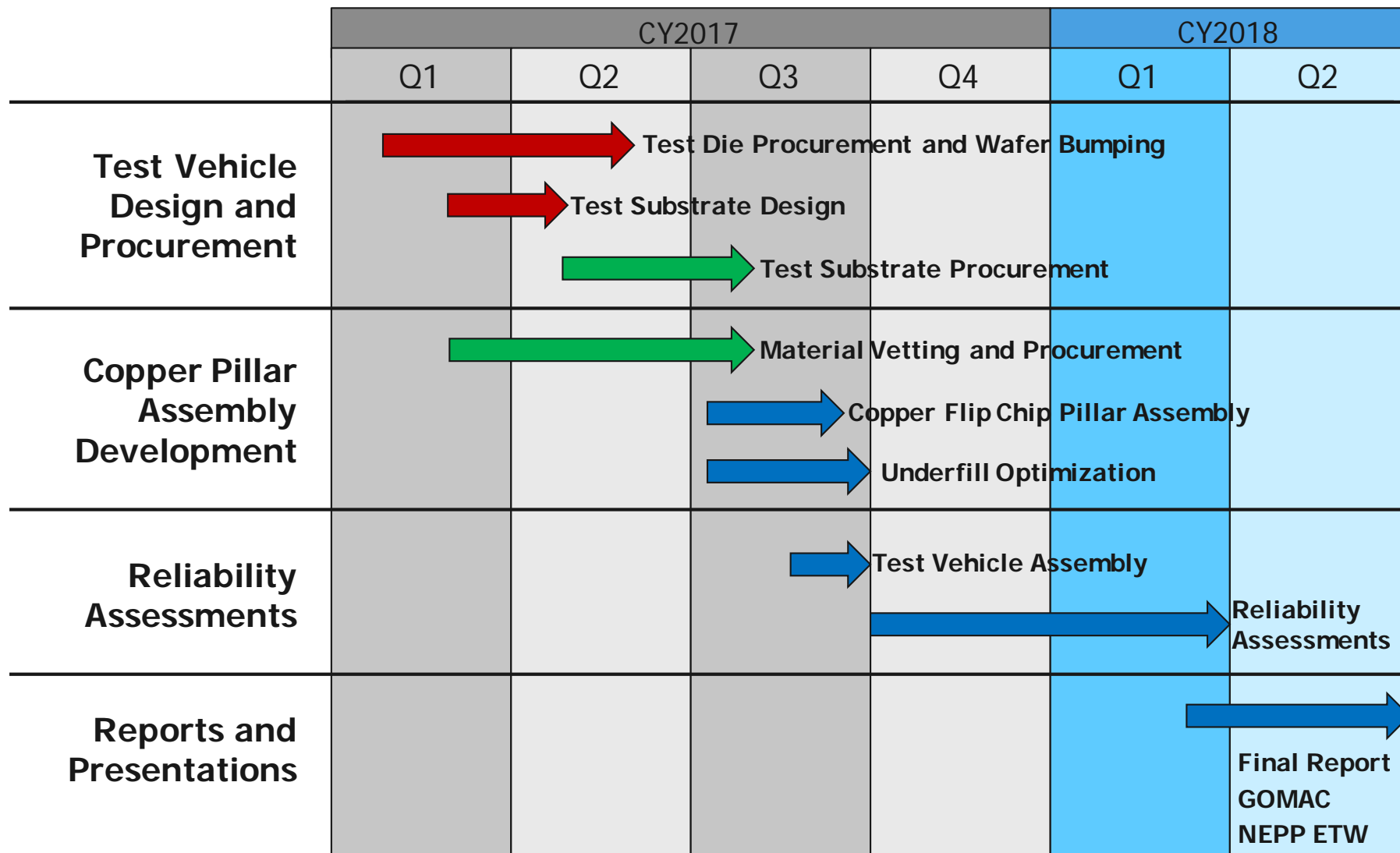
- *WC-150 Flip Chip Daisy Chain Test Die*
  - 150 $\mu$ m bump pitch; 40 $\mu$ m copper pillar bump, 25 $\mu$ m eutectic Sn/Pb solder cap
  - 10x10mm (3,718 I/O) and 20x20mm (14,872 I/O) die sizes
- *Organic High Density Build-Up (HDBU) test substrate*
  - Dual-sided, 1.0mm thick
  - 80 $\mu$ m solder mask defined pads with ENIG plating and eutectic SOP





# Fine Pitch Flip Chip on Organic Development

Cobham-NEPP Collaboration



# Next Generation Class Y Technology

Where are we going?

- Next Generation Class Y Technology
  - *Copper pillar flip chip on organic*
  - BGA second level interconnects instead of CGA
  - Use of BME decoupling capacitors?
  - New heat sink technologies?
  - Precursor to 2.5D/3D package technology qualification
- MIL-PRF-38535 Class Y
  - *Class Y currently does not accommodate organic substrates*
  - Should Class Y definition be amended/extended to capture Next Generation Class Y technology, or should a new designation be created?
- JEDEC Task Group
  - *When does it makes sense to create a dedicated task group chartered with evaluating Next Generation Class Y package technology?*
    - Is it too early? Is it too late?
  - Discuss further during September JEDEC meetings

***Next Generation Class Y Technology... to be continued***